

## CLAIMS

[1] Ultrahigh purity copper having a residual resistance ratio of 38,000 or greater and a purity of 8N or higher (excluding gas components of O, C, N, H, S and P).

5 [2] The ultrahigh purity copper according to claim 1, wherein the respective elements of O, C, N, H, S and P as gas components are 1ppm or less.

[3] A manufacturing method of ultrahigh purity copper, wherein, upon subjecting copper to high purification with the electrolytic method, an anode and a cathode are partitioned with an anion exchange membrane, an anolyte is intermittently or continuously extracted, active  
10 carbon is poured in and agitated so as to adsorb the impurities, and the obtained high purity copper electrolytic solution is intermittently or continuously introduced into the cathode side and electrolyzed.

[4] A manufacturing method of the ultrahigh purity copper according to claim 1 or claim 2, wherein, upon subjecting copper to high purification with the electrolytic method, an anode  
15 and a cathode are partitioned with an anion exchange membrane, an anolyte is intermittently or continuously extracted, active carbon is poured in and agitated so as to adsorb the impurities, and the obtained high purity copper electrolytic solution is intermittently or continuously introduced into the cathode side and electrolyzed.